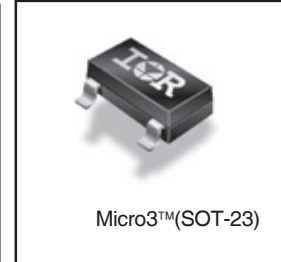
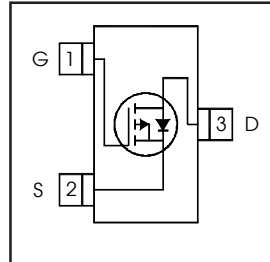


$V_{DS}$	<b>-20</b>	<b>V</b>
$R_{DS(on) max}$ (@ $V_{GS} = -4.5V$ )	<b>0.065</b>	$\Omega$
$Q_g$ (typical)	<b>8.0</b>	<b>nC</b>
$I_D$ (@ $T_A = 25^\circ C$ )	<b>-3.7</b>	<b>A</b>

HEXFET® Power MOSFET



Micro3™(SOT-23)

**Features**

Industry-standard pinout SOT-23 Package
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1, Industrial qualification



**Benefits**

Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRLML6402TRPbF-1	Micro3™ (SOT-23)	Tape and Reel	3000	IRLML6402TRPbF-1

**Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_{DS}$	Drain- Source Voltage	-20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-3.7	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-2.2	
$I_{DM}$	Pulsed Drain Current ①	-22	
$P_D @ T_A = 25^\circ C$	Power Dissipation	1.3	W
$P_D @ T_A = 70^\circ C$	Power Dissipation	0.8	
	Linear Derating Factor	0.01	W/°C
$E_{AS}$	Single Pulse Avalanche Energy④	11	mJ
$V_{GS}$	Gate-to-Source Voltage	± 12	V
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	°C

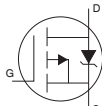
**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	75	100	°C/W

**Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	-0.009	—	V/°C	Reference to 25°C, I <sub>D</sub> = -1mA ②
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	0.050	0.065	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.7A ②
		—	0.080	0.135		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -3.1A ②
V <sub>GS(th)</sub>	Gate Threshold Voltage	-0.40	-0.55	-1.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
g <sub>fs</sub>	Forward Transconductance	6.0	—	—	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -3.7A ②
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	-1.0	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
		—	—	-25		V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 70°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	-100	nA	V <sub>GS</sub> = -12V
	Gate-to-Source Reverse Leakage	—	—	100		V <sub>GS</sub> = 12V
Q <sub>g</sub>	Total Gate Charge	—	8.0	12	nC	I <sub>D</sub> = -3.7A
Q <sub>gs</sub>	Gate-to-Source Charge	—	1.2	1.8		V <sub>DS</sub> = -10V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	2.8	4.2		V <sub>GS</sub> = -5.0V ②
t <sub>d(on)</sub>	Turn-On Delay Time	—	350	—	ns	V <sub>DD</sub> = -10V
t <sub>r</sub>	Rise Time	—	48	—		I <sub>D</sub> = -3.7A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	588	—		R <sub>G</sub> = 89Ω
t <sub>f</sub>	Fall Time	—	381	—		R <sub>D</sub> = 2.7Ω
C <sub>iss</sub>	Input Capacitance	—	633	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	145	—		V <sub>DS</sub> = -10V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	110	—		f = 1.0MHz

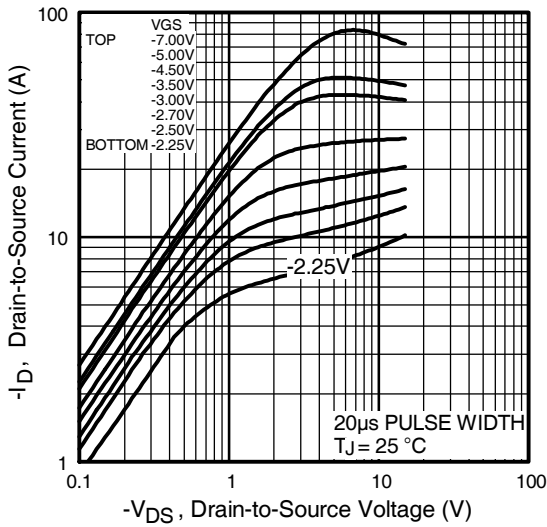
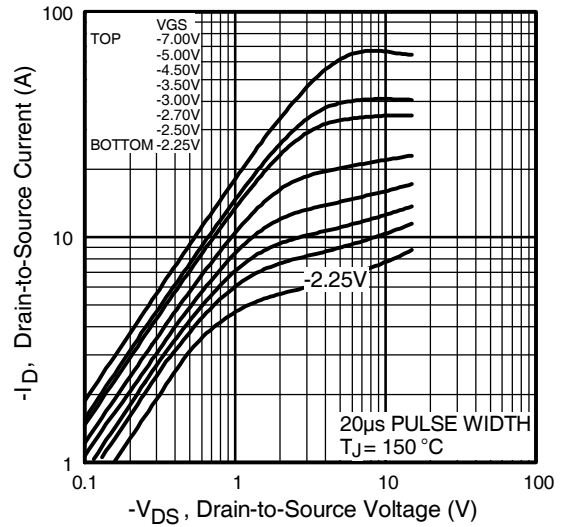
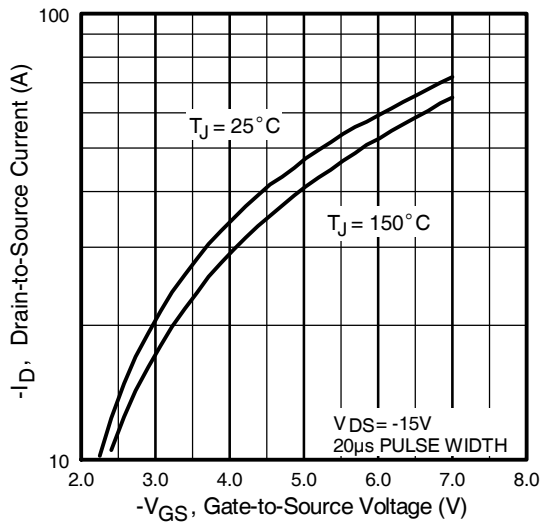
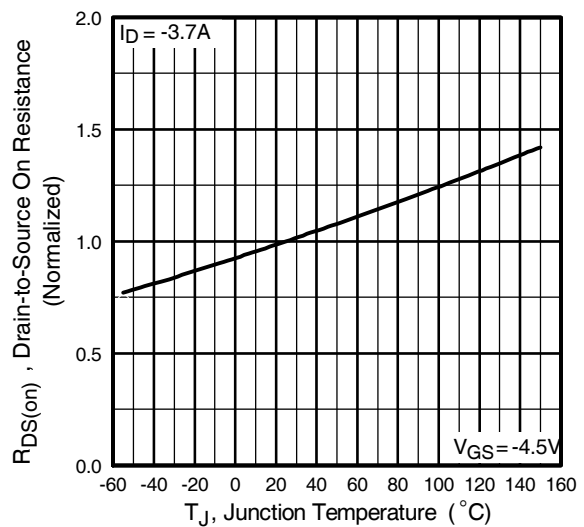
**Source-Drain Ratings and Characteristics**

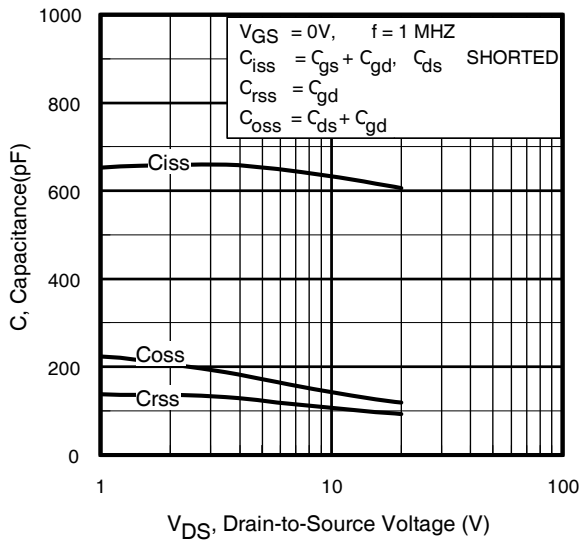
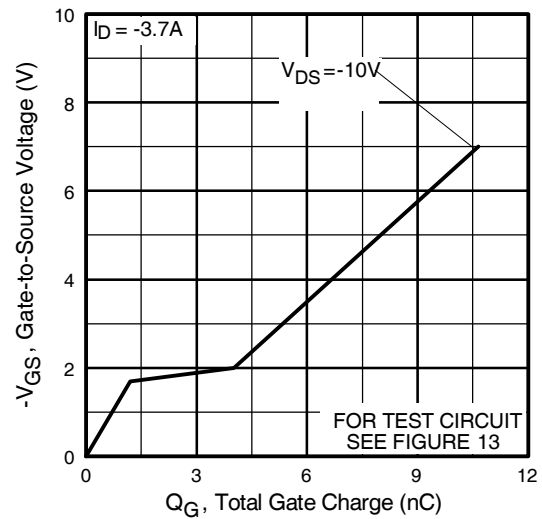
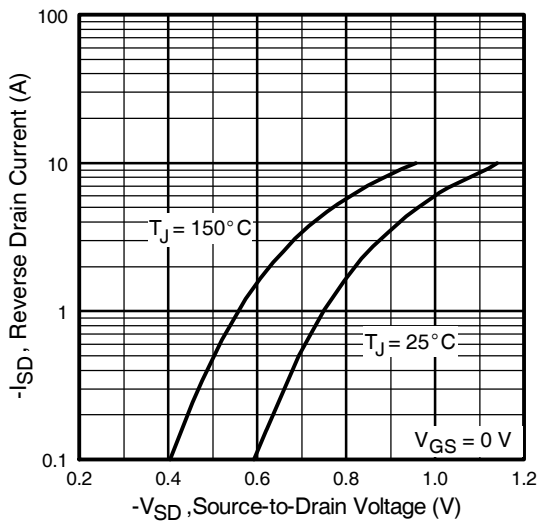
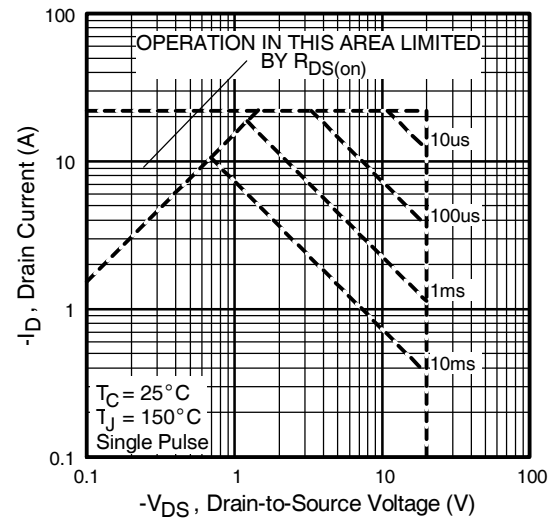
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	-1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	-22		
V <sub>SD</sub>	Diode Forward Voltage	—	—	-1.2	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = -1.0A, V <sub>GS</sub> = 0V ②
t <sub>rr</sub>	Reverse Recovery Time	—	29	43	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = -1.0A
Q <sub>rr</sub>	Reverse Recovery Charge	—	11	17	nC	di/dt = -100A/μs ②

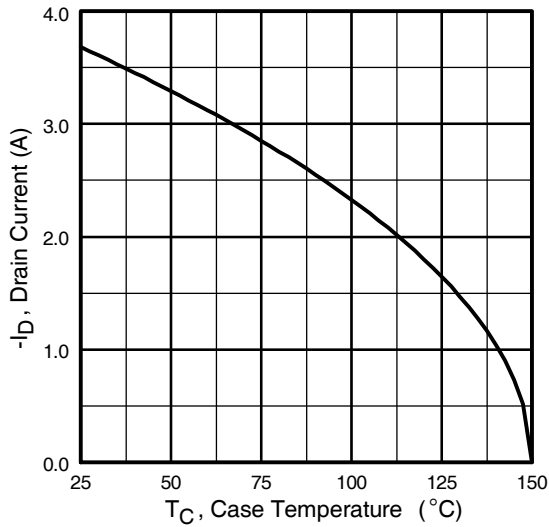
**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ③ Surface mounted on 1" square single layer 1oz. copper FR4 board, steady state.
- ④ Starting T<sub>J</sub> = 25°C, L = 1.65mH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = -3.7A.

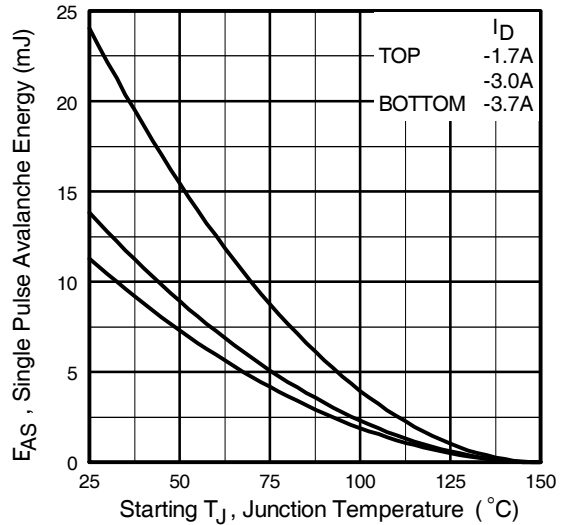
\*\* For recommended footprint and soldering techniques refer to application note #AN-994.


**Fig 1.** Typical Output Characteristics

**Fig 2.** Typical Output Characteristics

**Fig 3.** Typical Transfer Characteristics

**Fig 4.** Normalized On-Resistance Vs. Temperature

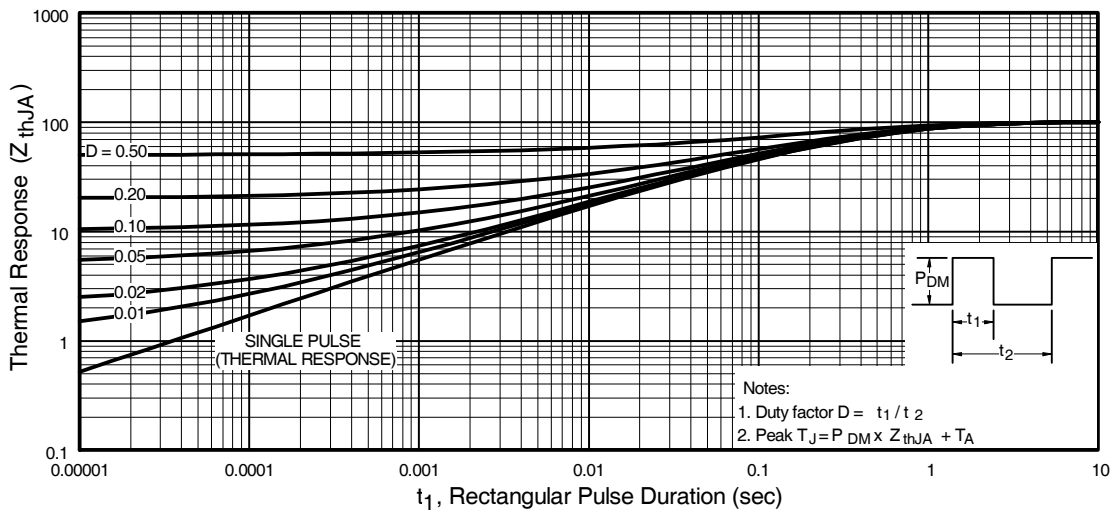

**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage

**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage

**Fig 7.** Typical Source-Drain Diode Forward Voltage

**Fig 8.** Maximum Safe Operating Area



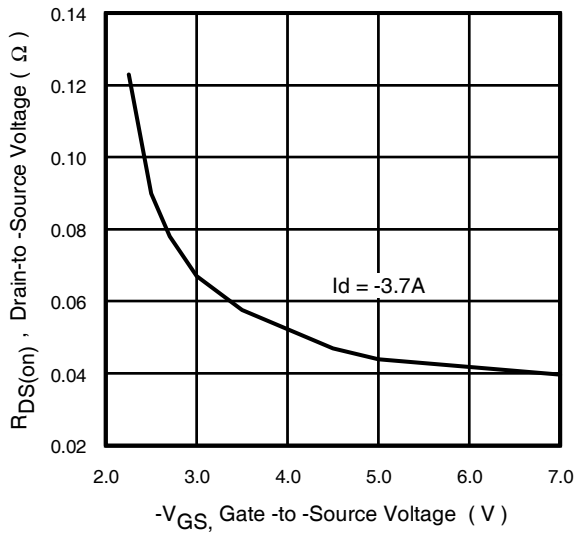
**Fig 9.** Maximum Drain Current Vs. Case Temperature



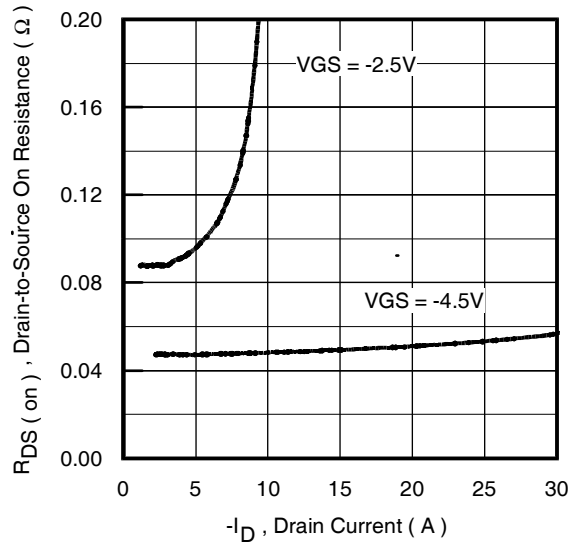
**Fig 10.** Maximum Avalanche Energy Vs. Drain Current



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



**Fig 12.** Typical On-Resistance Vs. Gate Voltage



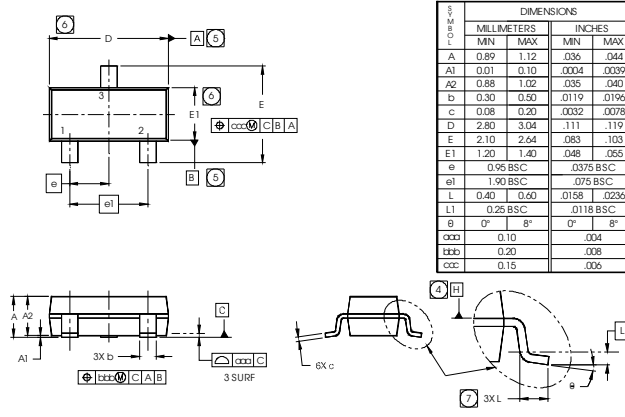
**Fig 13.** Typical On-Resistance Vs. Drain Current



# IRLML6402PbF-1

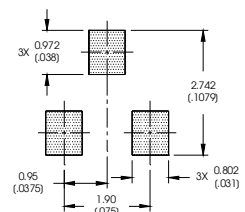
## Micro3 (SOT-23) (Lead-Free) Package Outline

Dimensions are shown in millimeters (inches)



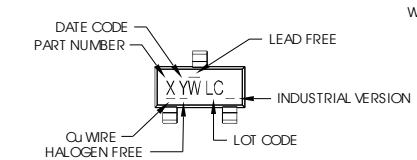
DIMENSION	DIMENSIONS			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.89	1.12	.036	.044
A1	0.01	0.10	.0004	.0039
A2	0.88	1.02	.035	.040
b	0.30	0.50	.0119	.0196
c	0.08	0.20	.0032	.0078
D	2.80	3.04	.111	.119
E	2.10	2.64	.083	.103
E1	1.20	1.40	.048	.055
e	0.95 BSC		.0375 BSC	
e1	1.90 BSC		.075 BSC	
L	0.40	0.60	.0158	.0236
L1	0.25 BSC		.0118 BSC	
B	0"	8"	0"	8"
0000	0.10		.004	
0000	0.20		.008	
0000	0.15		.006	

### RECOMMENDED FOOTPRINT



- NOTES
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS AND INCHES.
  3. CONTROLLING DIMENSION: MILLIMETER.
  4. DATUM PLANE H IS LOCATED AT THE MOLD PARTING LINE.
  5. DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
  6. DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H.
  7. DIMENSION L IS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE.
  8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-236AB.

## Micro3 (SOT-23 / TO-236AB) Part Marking Information



- X = PART NUMBER CODE REFERENCE:
- |               |               |
|---------------|---------------|
| A = IRLML2402 | S = IRLML6244 |
| B = IRLML2803 | T = IRLML6246 |
| C = IRLML6302 | U = IRLML6344 |
| D = IRLML5103 | V = IRLML6346 |
| E = IRLML6402 | W = IRFML8244 |
| F = IRLML6401 | X = IRLML2244 |
| G = IRLML2502 | Y = IRLML2246 |
| H = IRLML5203 | Z = IRFML9244 |
| I = IRLML0030 |               |
| J = IRLML2030 |               |
| K = IRLML0100 |               |
| L = IRLML0060 |               |
| M = IRLML0040 |               |
| N = IRLML2060 |               |
| P = IRLML9301 |               |
| R = IRLML9303 |               |

Note: A line above the work week (as shown here) indicates Lead-Free.

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Y	WORK WEEK	W	
2011	2001	1	01	A
2012	2002	2	02	B
2013	2003	3	03	C
2014	2004	4	04	D
2015	2005	5		
2016	2006	6		
2017	2007	7		
2018	2008	8		
2019	2009	9		
2020	2010	0	24	X
			25	Y
			26	Z

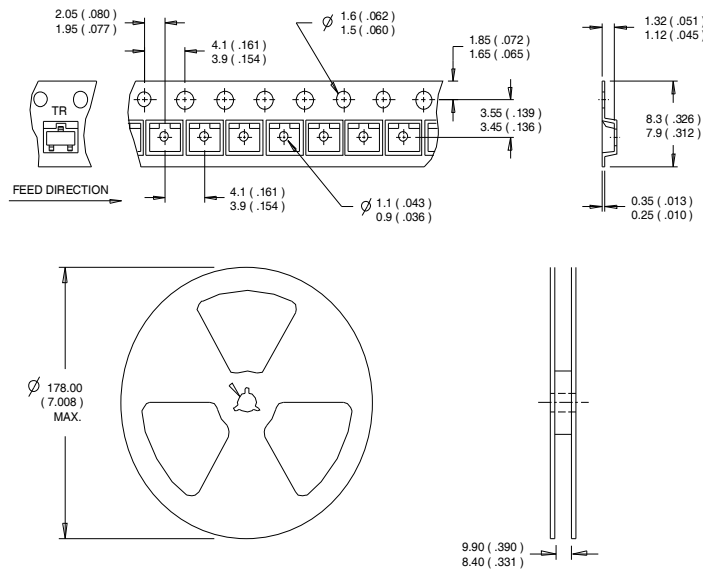
W = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W	
2011	2001	A	27	A
2012	2002	B	28	B
2013	2003	C	29	C
2014	2004	D	30	D
2015	2005	E		
2016	2006	F		
2017	2007	G		
2018	2008	H		
2019	2009	J		
2020	2010	K	50	X
			51	Y
			52	Z

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

## Micro3™(SOT-23/TO-263AB) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES:  
 1. CONTROLLING DIMENSION : MILLIMETER.  
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

### Qualification information†

Qualification level	Industrial (per JEDEC JESD47F <sup>††</sup> guidelines)	
Moisture Sensitivity Level	Micro3™ (SOT-23)	M6L1 (per JEDEC J-STD-020D <sup>††</sup> )
RoHS compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

†† Applicable version of JEDEC standard at the time of product release

### Revision History

Date	Comment
10/28/2014	• Updated partmarking to reflect Industrial partmarking on page 7.

International  
 Rectifier

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA

To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>



单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon Technologies\(英飞凌\)](#)